

line 15, delete "the" (second occurrence) and insert --a--.

Page 17, line 8, delete "or laser" and insert --(mechanical or laser)--.

IN THE CLAIMS:

1. (Amended) A process for manufacturing a semiconductor device comprising [the] steps of:

defining a [number] plurality of semiconductor chip sections on a wafer, each semiconductor chip section having a [number] plurality of chip electrodes formed on one surface along a periphery thereof, the one surface being covered with a passivating film except for [the] positions where the chip electrodes are formed;

forming a number of interconnection layers on the wafer for each semiconductor chip section such that each interconnection layer is connected to the chip electrode at [one] a first end thereof and is extended inwardly toward the chip section at [the other] a second end;

AM covering [the] an entire surface of the wafer with a cover coating film; forming a [number] plurality of apertures in the cover coating film, the apertures being formed into a matrix;

simultaneously forming a [number] plurality of bumps on the respective apertures; and

separating the semiconductor chip sections on the wafer as individual semiconductor chips along scribe lines.

2. (Amended) A process for manufacturing a semiconductor device as claimed in claim 1, wherein the interconnection layer is extended inwardly at a position where the semiconductor chip section is exposed to the atmosphere through the aperture.

AS 4. (Amended) A process for manufacturing a semiconductor device as claimed in claim 1, wherein the bumps are formed at the position except for [just] over the chip electrodes.

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1 5. (Amended) A semiconductor wafer having a [number] plurality of
2 semiconductor chips, comprising:

3 bump electrodes simultaneously formed into a matrix on an entire
4 surface of the wafer except for on scribe lines between the semiconductor
5 chips.

1 6. (Amended) A process for manufacturing a semiconductor device having a
2 [number] plurality of chip electrodes, a [number] plurality of bump electrodes,
3 and interconnecting layers for respectively electrically connecting the chip
4 electrodes and the bump electrodes, the process comprising [the] steps of:

5 providing a wafer having a [number] plurality of chip sections defined
6 thereon by scribe lines, each chip section having the chip electrodes formed
7 thereon;

cont
8 providing the interconnection layers such that each interconnection layer
9 is connected to the chip electrode at [one] a first end thereof and [the other] a
10 second end of the interconnection layer is extended towards [the] a central
11 portion of the chip section;

12 applying a coating film over [the] an entire surface of the wafer and the
13 interconnection layers;

14 forming a [number] a plurality of apertures in the coating film passing
15 therethrough;

16 simultaneously forming the bump electrodes at [the] a position
17 corresponding to the apertures; and

18 separating the chip sections from each other along the scribe lines.

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1 9. (Amended) A process for manufacturing a semiconductor device as
2 claimed in claim 6, wherein the bump electrodes are located at positions other
than [the place just] over the chip electrodes.

1 10. (Amended) A semiconductor wafer, including:

2 [having] a [number] plurality of chip sections defined thereon by scribe